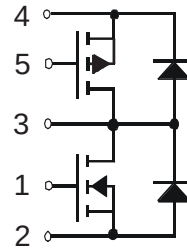


Trench™ P & N-Channel Power MOSFET Common Drain Topology

FMP76-01T



	P CH.	N CH.
V_{DSS}	- 100V	100V
I_{D25}	- 54A	62A
$R_{DS(on)}$	24mΩ	11mΩ
$t_{rr(typ)}$	70ns	67ns

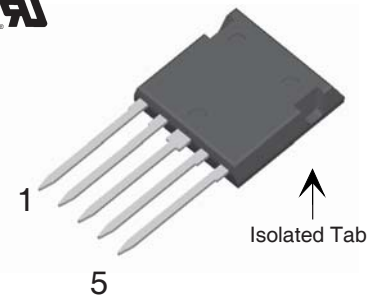
Symbol	Test Conditions	Maximum Ratings	
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
V_{ISOLD}	50/60Hz, RMS, t = 1min, leads-to-tab	2500	~V
T_L	1.6mm (0.062 in.) from case for 10s	300	°C
T_{SOLD}	Plastic body for 10s	260	°C
F_C	Mounting force	20..120 / 4.5..27	N/lb.

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
C_p	Coupling capacitance between shorted pins and mounting tab in the case		40	pF
d_S, d_A	pin - pin	1.7		mm
d_S, d_A	pin - backside metal	5.5		mm
Weight			9	g

P - CHANNEL

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^{\circ}\text{C}$ to 150°C	- 100	V
V_{DGR}	$T_J = 25^{\circ}\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	- 100	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^{\circ}\text{C}$	- 54	A
I_{DM}	$T_C = 25^{\circ}\text{C}$, pulse width limited by T_{JM}	- 230	A
I_A	$T_C = 25^{\circ}\text{C}$	- 38	A
E_{AS}	$T_C = 25^{\circ}\text{C}$	1.0	J
P_D	$T_C = 25^{\circ}\text{C}$	132	W

ISOPLUS i4-Pak™



Features

- Silicon chip on Direct-Copper Bond (DCB) substrate
 - UL recognized package
 - Isolated mounting surface
 - 2500V electrical isolation
- Avalanche rated
- Low Q_g
- Low Drain-to-Tab capacitance
- Low package inductance

Advantages

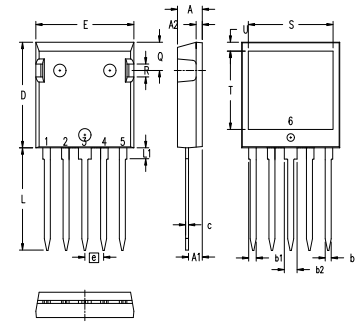
- Low gate drive requirement
- High power density
- Low drain to ground capacitance
- Fast switching

Applications

- DC and AC motor drives
- Class AB audio amplifiers
- Multi-phase DC to DC converters
- Industrial battery chargers
- Switching power supplies

Symbol	Test Conditions ² (T _J = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = - 250 μA	- 100		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250μA	- 2.0		- 4.0 V
I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0V			± 100 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 125°C			-15 μA - 750 μA
R _{DS(on)}	V _{GS} = -10V, I _D = - 38A, Note 1			24 mΩ
g _{fs}	V _{DS} = -10V, I _D = - 38A, Note 1	35	58	S
C _{iss}	V _{GS} = 0V, V _{DS} = - 25V, f = 1MHz		13.7	nF
C _{oss}			890	pF
C _{rss}			275	pF
t _{d(on)}	Resistive Switching Times V _{GS} = -10V, V _{DS} = 0.5 • V _{DSS} , I _D = - 38A R _G = 1Ω (External)		25	ns
t _r			40	ns
t _{d(off)}			52	ns
t _f			20	ns
Q _{g(on)}	V _{GS} = -10V, V _{DS} = 0.5 • V _{DSS} , I _D = - 38A		197	nC
Q _{gs}			65	nC
Q _{gd}			65	nC
R _{thJC}				0.95 °C/W
R _{thCS}		0.15		°C/W

ISOPLUS i4-Pak™ Outline



NOTE: Bottom heatsink meets 3000 Volts AC 1 sec isolation to the other pins.

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
b2	.100	.110	2.54	2.79
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

Ref: IXYS CO 0077 R0

Drain-Source Diode

Symbol	Test Conditions ²	Characteristic Values		
		Min.	Typ.	Max.
I _s	V _{GS} = 0V			- 54 A
I _{SM}	Repetitive, pulse width limited by T _{JM}			- 304 A
V _{SD}	I _F = - 38A, V _{GS} = 0V, Note 1			- 1.3 V
t _{rr}	I _F = - 38A, di/dt = 100A/μs V _R = - 50V, V _{GS} = 0V		70	ns
Q _{RM}			215	nC
I _{RM}			- 6	A

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

N - CHANNEL

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	100	V
V_{DGR}	$T_J = 25^{\circ}\text{C to } 150^{\circ}\text{C}, R_{GS} = 1\text{M}\Omega$	100	V
V_{GSM}	Transient	± 20	V
I_{D25}	$T_C = 25^{\circ}\text{C}$	62	A
I_{DM}	$T_C = 25^{\circ}\text{C}$, pulse width limited by T_{JM}	300	A
I_A	$T_C = 25^{\circ}\text{C}$	65	A
E_{AS}	$T_C = 25^{\circ}\text{C}$	500	mJ
P_D	$T_C = 25^{\circ}\text{C}$	89	W

Symbol	Test Conditions ² ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{V}, I_D = 250\text{ }\mu\text{A}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{V}$			$\pm 200\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{V}$ $T_J = 150^{\circ}\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 25\text{A}$, (Note 1)			11 m Ω
g_{fs}	$V_{DS} = 10\text{V}, I_D = 60\text{A}$, (Note 1)	55	93	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	5080		pF
C_{oss}				635 pF
C_{rss}				95 pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 25\text{A}$ $R_G = 5\Omega$ (External)	30		ns
t_r		47		ns
$t_{d(off)}$		44		ns
t_f		28		ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 25\text{A}$	104		nC
Q_{gs}		30		nC
Q_{gd}		29		nC
R_{thJC}				1.4 $^{\circ}\text{C/W}$
R_{thCS}		0.15		$^{\circ}\text{C/W}$

Source-Drain Diode
Characteristic Values
 $T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Conditions ³	Min.	Typ.	Max.
I_S	$V_{GS} = 0V$			62 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			350 A
V_{SD}	$I_F = 25A$, $V_{GS} = 0V$, Note 1			1.0 V
t_{rr}	$I_F = 25A$, $-di/dt = 100A/\mu s$ $V_R = 50V$, $V_{GS} = 0V$		67	ns
Q_{RM}			160	nC
I_{RM}			4.7	A

Note 1: Pulse test, $t \leq 300\mu s$, duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated objective result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.